



National
Semiconductor™

Discrete POWER & Signal
Technologies

Pro Electron Surface Mount Diodes

Device No.	V _{rrm} (V) Min	I _{rrm} (mA) Min	V _{fm} (V) Max	V _{fm} @ I _f (mA)	t _{rr} (ns) Max	Package No.	Process No.
BAS16	75	1000	1	100	50	TO-236AB	1R
BAS19	100	100	1	100	50	TO-236AB	1J
BAS20	150	100	1	100	50	TO-236AB	1J
BAS21	200	100	1	100	50	TO-236AB	1J
BAS29	90	100	1	200	50	TO-236AB	1J
BAS31	90	100	1	200	50	TO-236AB	1J
BAS35	90	100	1	200	50	TO-236AB	1J
BAV70	70	2500	1	50	6	TO-236AB	1R
BAV74	50	100	1	100	4	TO-236AB	1R
BAV99	70	2500	1	50	6	TO-236AB	1R (3-19)
BAW56	70	2500	1	50	6	TO-236AB	1R

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (**section-page**) of device datasheet.